

REMARKS

This is in response to the Office Action dated September 25, 2003. Claims 14-15 have been canceled. Thus, claims 1-13 and 16 are now pending.

For purposes of example, and without limitation, certain example embodiments of this invention relate to a method of making a semiconductor device including a silicide film in at least a source/drain region. In the Fig. 1 embodiment for example, source/drain regions 16, 17 are formed so as to be supported by a semiconductor substrate 11. Native oxides 18 naturally form over the source/drain regions as shown in Fig. 1A. A first metal inclusive film (e.g., Ti) 20 is formed over the substrate as shown in Fig. 1B. Thereafter, a thermal treatment is performed in order to cause the Ti to react thereby causing the native oxides to be reduced and also to cause a silicide film 25 to form over or in the source/drain regions as shown in Fig. 1C. At least an unreacted part of the first metal inclusive film is then removed. Thereafter, a second metal inclusive film (e.g., Co) 21 is formed over at least part of the substrate. Another thermal treatment is performed to cause the Co to react thereby causing a second silicide film 22 to form at least partially in *source/drain region(s)* where the first silicide 25 was formed as shown in Fig. 1D. Example advantages associated with certain embodiments of this invention (e.g., avoiding disadvantages such as the silicide not forming due to native oxide existence) are discussed on page 14 of the instant specification.

Claim 1 stands rejected under 35 U.S.C. Section 103(a) as being allegedly unpatentable over Kimura in view of Iinuma. This Section 103(a) rejection is respectfully traversed for at least the following reasons.

Claim 1 requires that the first and second silicide films are formed in the *source/drain region*. Kimura, the base reference, fails to disclose or suggest this aspect of claim 1. Instead, Kimura teaches directly away from this aspect of claim 1 by forming silicide only over the gate. Thus, it can be seen that Kimura is entirely unrelated to this aspect of claim 1. The cited art is completely silent as to provided the first and second claimed silicide films on source/drain region(s) as called for in claim 1.

Moreover, one of ordinary skill in the art would never have modified Kimura to provide the first and second silicide films in the source/drain region(s) because Kimura's insulating film 44 would prevent the second silicide film 45/41 from being formed on the source/drain region in any meaningful manner (see Figs. 32-34 of Kimura, which illustrates that the alleged second silicide film is formed over insulator 44). Again, Kimura teaches directly away from the invention of claim 1 in this respect. Citation to other art cannot cure the aforesaid fundamental flaws of Kimura.

Claims 12 and 13 also require that the first and second silicide films are formed in or on the *source/drain region*. Again, the cited art fails to disclose or suggest this aspect(s) of these claims.

For at least the foregoing reasons, it is respectfully requested that all rejections be withdrawn. All claims are now in condition for allowance. If any minor matter remains

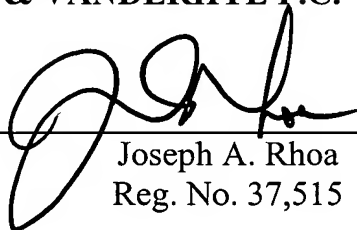
SOTOME, Yoshihiro
Appl. No. 10/038,580
December 16, 2003

to be resolved, the Examiner is invited to telephone the undersigned with regard to the same.

Respectfully submitted,

NIXON & VANDERHYE P.C.

By: _____



Joseph A. Rhoa
Reg. No. 37,515

JAR: caj
1100 North Glebe Road, 8th Floor
Arlington, VA 22201-4714
Telephone: (703) 816-4000
Facsimile: (703) 816-4100